

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- Enhanced power dissipation capability of 1115 mW

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5.6	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 4.5 A; T _j = 25 °C		-	31	36	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D L
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G 017aaa253

6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMV37EN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMV37EN2	%К7

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

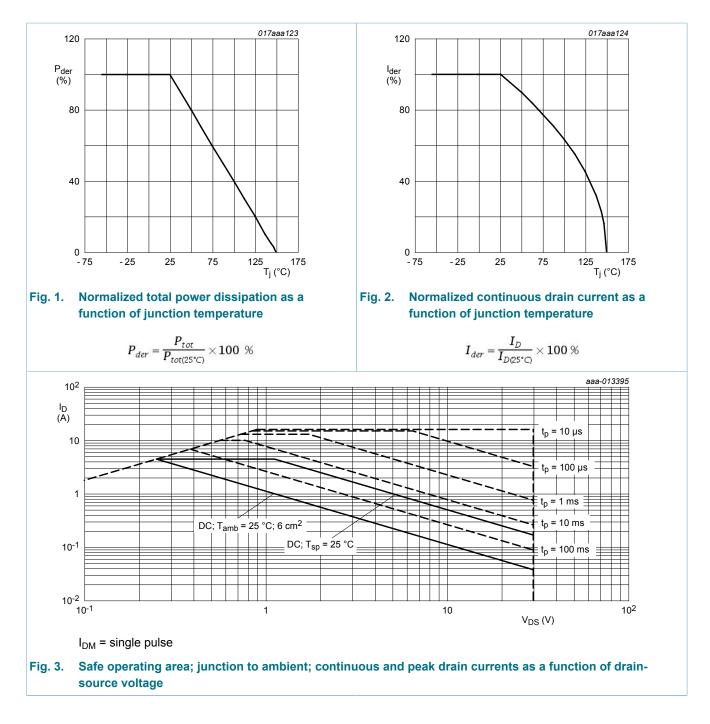
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	5.6	А
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.5	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.8	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	16	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	1115	mW
		T _{sp} = 25 °C		-	5000	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
ls	source current	T _{amb} = 25 °C	[1]	-	1	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	209	246	K/W
			[2]	-	95	112	K/W
		in free air; t ≤ 5 s	[2]	-	63	72	K/W

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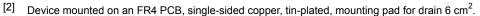
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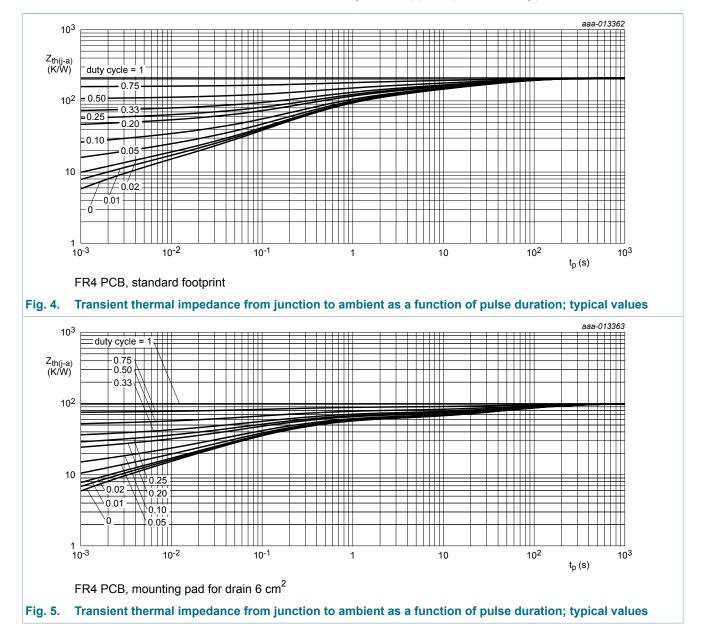
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	20	25	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



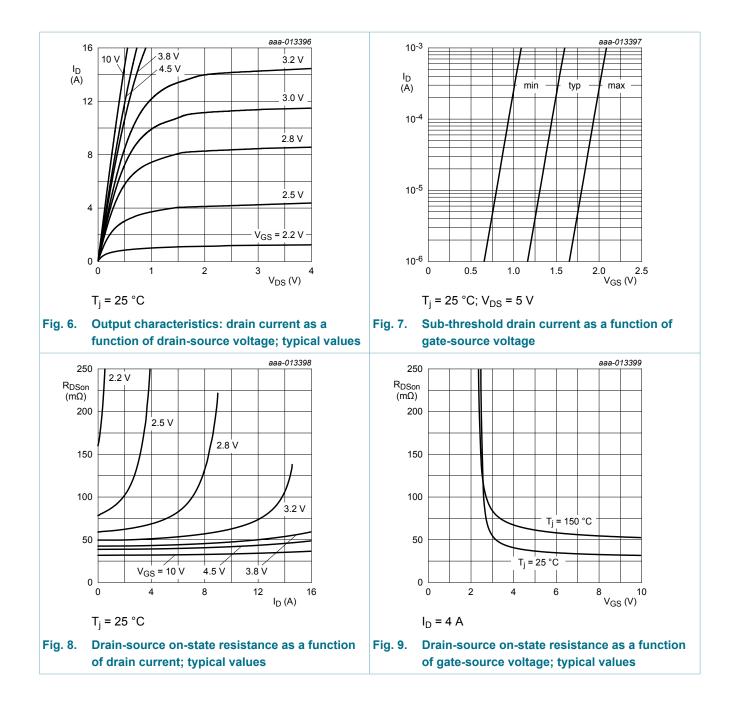


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C	1	1.5	2	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 4.5 A; T _j = 25 °C	-	31	36	mΩ
resistance	resistance	V_{GS} = 10 V; I _D = 4.5 A; T _j = 150 °C	-	48	56	mΩ
		V_{GS} = 4.5 V; I _D = 3.9 A; T _j = 25 °C	-	37	47	mΩ
9fs	forward transconductance	V _{DS} = 10 V; I _D = 2 A; T _j = 25 °C	-	10	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	7	-	Ω
Dynamic cl	naracteristics		I.			
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V;	-	3.6	6.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.5	-	nC
Q _{GD}	gate-drain charge		-	0.4	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	209	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	50	-	pF
C _{rss}	reverse transfer capacitance		-	17	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	12	-	ns
t _{d(off)}	turn-off delay time	1	-	11	-	ns
t _f	fall time		-	2	-	ns
Source-dra	in diode		1	1		
V _{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _i = 25 °C	-	0.75	1.2	V

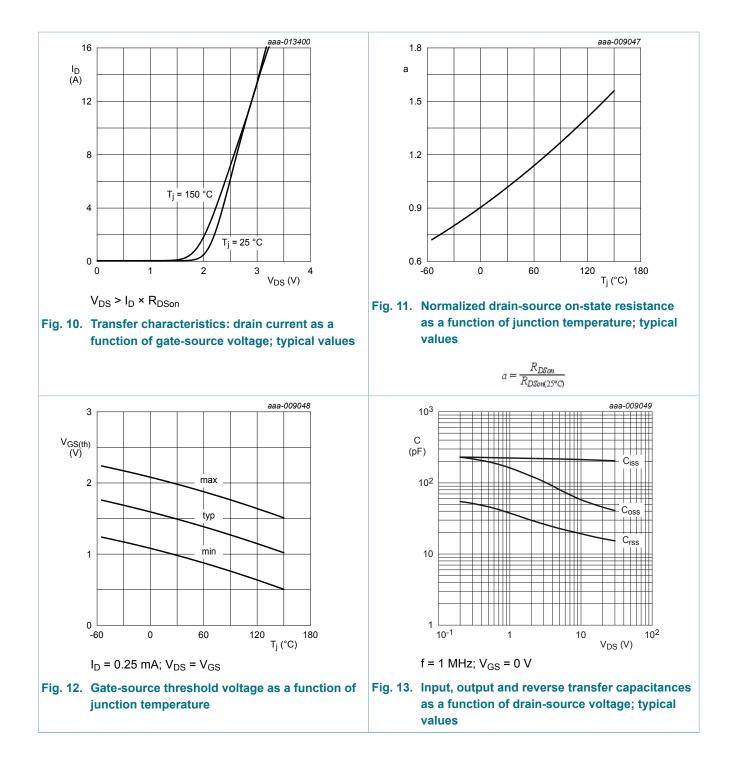
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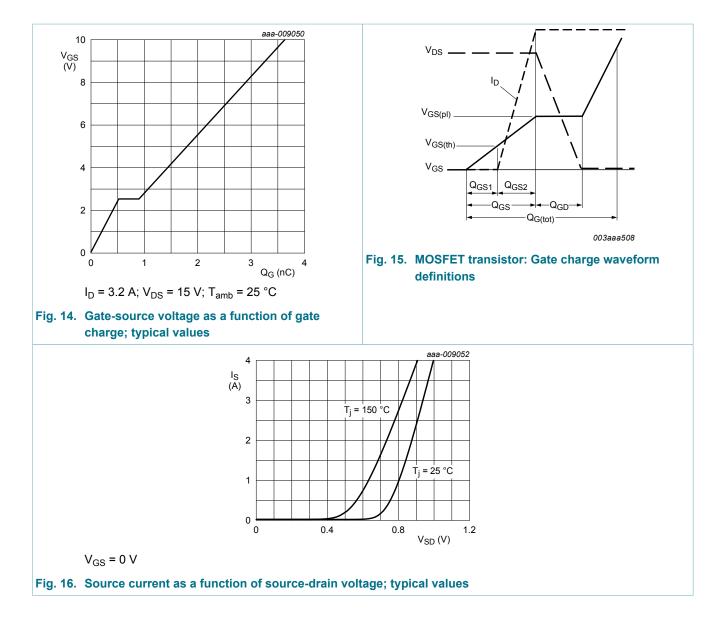
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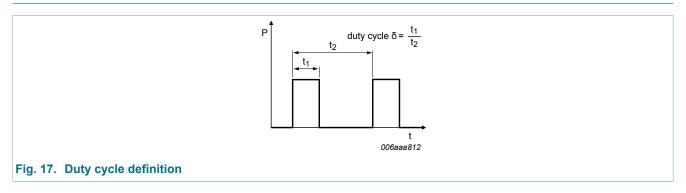


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11. Test information



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12. Package outline

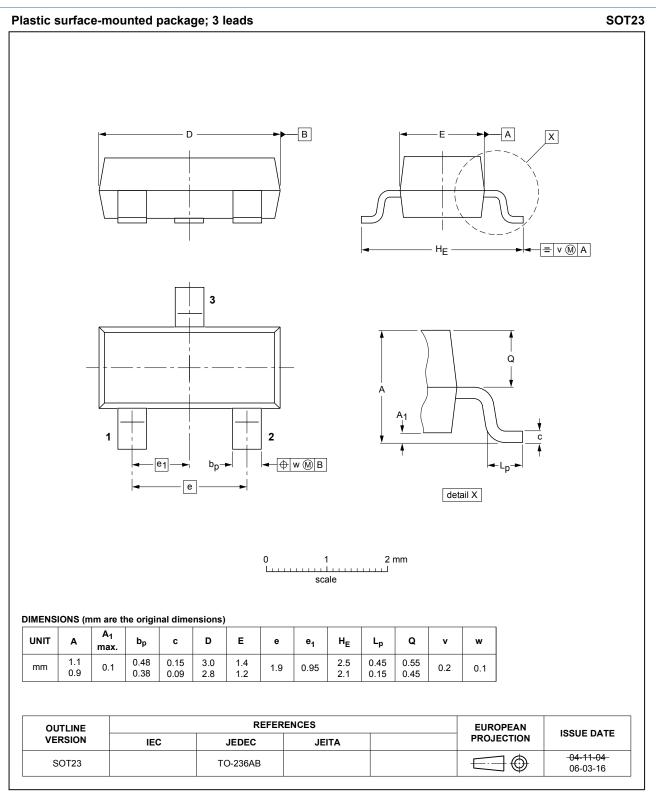


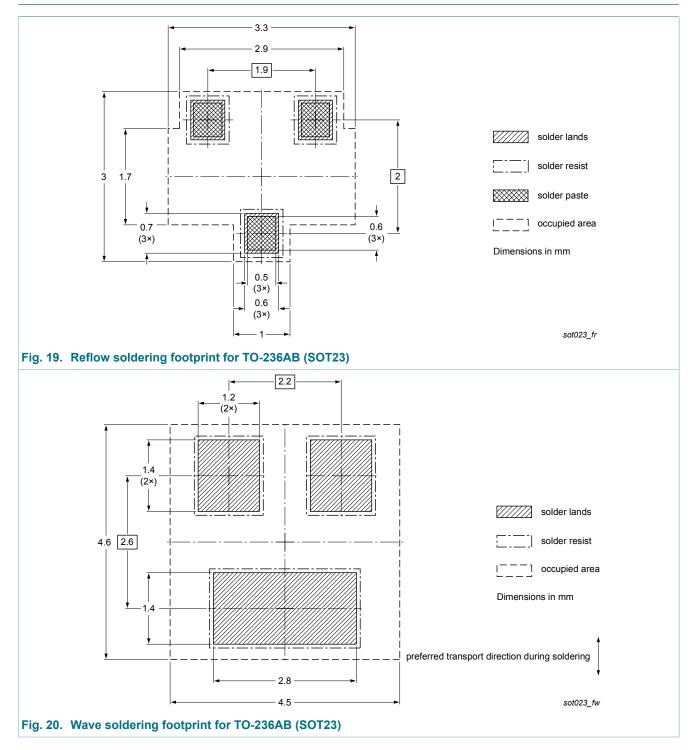
Fig. 18. Package outline TO-236AB (SOT23)

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13. Soldering



14. Revision history

Table 8. Revision his	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV37EN2 v.1	20140603	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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